



The University of Manchester National Graphene Institute

Superconductivity-induced features in the electronic Raman spectrum of monolayer graphene

Raman scattering minds the gap

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Image from "Raman Spectroscopy in Graphene Related Systems" Ado Jorio et al.

Outline

- ERS in graphene
 - Graphene
 - Raman in graphene
 - Electronic Raman scattering in graphene
- ERS in superconducting graphene
 - Superconducting graphene
 - Electronic Raman scattering in superconducting graphene

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Raman scattering in graphene



Raman scattering in graphene: defects



Raman scattering in graphene: layers



Raman scattering in graphene: strains



Raman scattering in graphene: strains





ERS in graphene: the picture

—Virtual state



ERS in graphene: the picture



ERS in graphene: the picture

—Virtual state





ERS in graphene: the theory

XY – configuration



ERS in graphene: the experiment



ERS in graphene: the experiment



"Thus one can see that electronic Raman scattering at zero magnetic field is a sensitive tool for probing the low-energy electronic structure and pseudospin symmetry in pure and doped graphitic structures, and it has a potential for studying gapped structures formed by different methods.

ERS in graphene: the experiment



Outline

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ERS in superconducting graphene: the picture





ERS in superconducting graphene: the picture









The challenge: Is this feature measurable?

Quantum
efficiency
$$= \int d\omega \int d \begin{pmatrix} scattered \\ angles \end{pmatrix} w(\omega) \sim 10^{-14}$$





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Extra slide: peak at 117cm⁻¹

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[...] the XX spectrum of the annealed sample demonstrates a surprising appearance of the narrow intense band at 117 cm⁻¹ (see Fig. S3 in [30]). Its line shape is very asymmetric, showing the well-known Breit-Wigner-Fano (BWF) interference between the phonon and continuum [33]. This implies the **appearance of the defect-induced low-energy electronic excitations, perhaps of the intraband type discussed in [16,17].**



Supplementary information

The heat treatment results in a strong intensity increase of the D mode at 1346 cm⁻¹ and an appearance of asymmetric low-frequency peak at 117 cm⁻¹. This implies a growth of the defect density leading to selection rules violation and Raman activity of layerbreathing mode at 117 cm⁻¹.



